NSN 5961-01-034-2232

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View Online at https://aerobasegroup.com/nsn/5961-01-034-2232 **Inclosure Material:** Metal **Overall Length:** 1.125 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 1.031 inches and 1.062 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1.8 forward voltage, total rms and 100.0 breakover voltage, dc **Current Rating Per Characteristic:** 150.00 amperes source cutoff current preset and 40.00 milliamperes forward current, total rms peak **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 uninsulated wire lead w/terminal lug **Specification Data:** 81349-mil-prf- 19500 government specification Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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Mil-std (military Standard):

Mil-prf-19500 spec.